74AUP1T97

Low-power configurable gate with voltage-level translator Rev. 2 — 18 October 2010 Product data s

Product data sheet

General description 1.

The 74AUP1T97 provides low-power, low-voltage configurable logic gate functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 2.3 V to 3.6 V.

The 74AUP1T97 is designed for logic-level translation applications with input switching levels that accept 1.8 V low-voltage CMOS signals, while operating from either a single 2.5 V or 3.3 V supply voltage.

The wide supply voltage range ensures normal operation as battery voltage drops from 3.6 V to 2.3 V.

This device is fully specified for partial power-down applications using I_{OFF}.

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger inputs make the circuit tolerant to slower input rise and fall times across the entire V_{CC} range.

Features and benefits 2.

- Wide supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 1.5 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power configurable gate with voltage-level translator

3. Ordering information

Table 1. Ordering information

| Type number | Package | | | | | | | |
|-------------|-------------------|-------|---|---------|--|--|--|--|
| | Temperature range | Name | Description | Version | | | | |
| 74AUP1T97GW | -40 °C to +125 °C | SC-88 | plastic surface-mounted package; 6 leads | SOT363 | | | | |
| 74AUP1T97GM | –40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm | SOT886 | | | | |
| 74AUP1T97GF | –40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm | SOT891 | | | | |
| 74AUP1T97GN | –40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm | SOT1115 | | | | |
| 74AUP1T97GS | –40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm | SOT1202 | | | | |

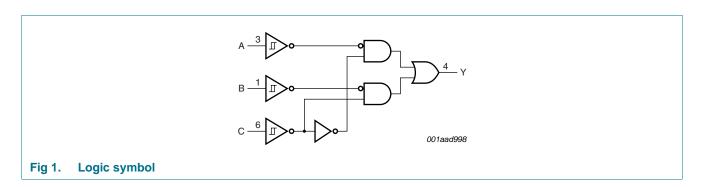
4. Marking

Table 2. Marking

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| 74AUP1T97GW | 59 |
| 74AUP1T97GM | 59 |
| 74AUP1T97GF | 59 |
| 74AUP1T97GN | 59 |
| 74AUP1T97GS | 59 |

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

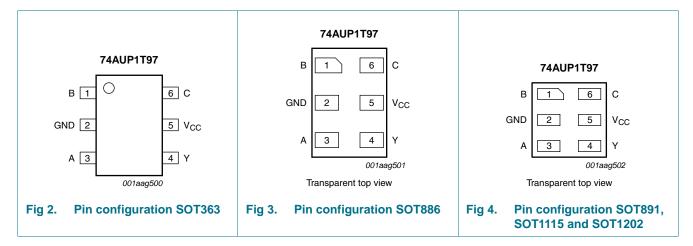
5. Functional diagram



Low-power configurable gate with voltage-level translator

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|-----------------|-----|----------------|
| В | 1 | data input |
| GND | 2 | ground (0 V) |
| A | 3 | data input |
| Υ | 4 | data output |
| V _{CC} | 5 | supply voltage |
| С | 6 | data input |

7. Functional description

Table 4. Function table[1]

| Input | | | Output |
|-------|---|---|--------|
| С | В | Α | Υ |
| L | L | L | L |
| L | L | Н | L |
| L | Н | L | Н |
| L | Н | Н | Н |
| Н | L | L | L |
| Н | L | Н | Н |
| Н | Н | L | L |
| Н | Н | Н | Н |

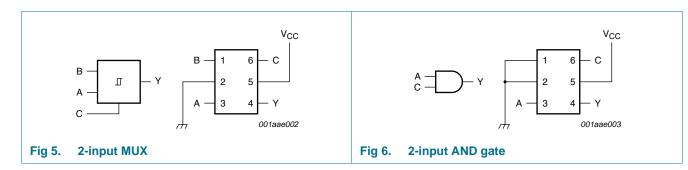
^[1] H = HIGH voltage level; L = LOW voltage level.

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7.1 Logic configurations

Table 5. Function selection table

| Logic function | Figure |
|--------------------------------------|---------------|
| 2-input MUX | see Figure 5 |
| 2-input AND | see Figure 6 |
| 2-input OR with one input inverted | see Figure 7 |
| 2-input NAND with one input inverted | see Figure 7 |
| 2-input AND with one input inverted | see Figure 8 |
| 2-input NOR with one input inverted | see Figure 8 |
| 2-input OR | see Figure 9 |
| Inverter | see Figure 10 |
| Buffer | see Figure 11 |



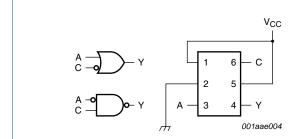


Fig 7. 2-input NAND gate with input A inverted or 2-input OR gate with input C inverted

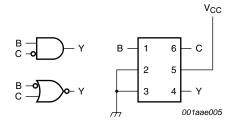
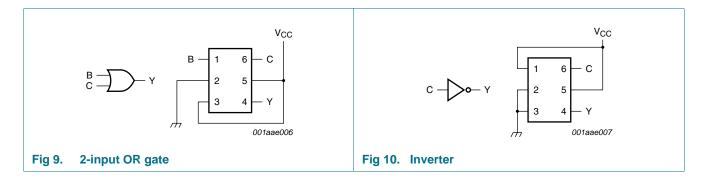
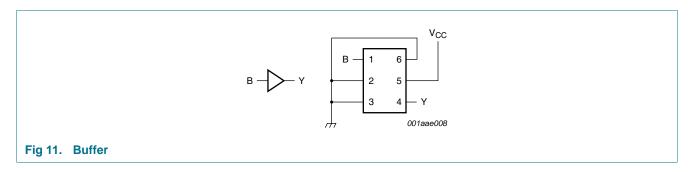


Fig 8. 2-input NOR gate with input B inverted or 2-input AND gate with input C inverted



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8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol Parameter Conditions Min Max | t Unit |
|--|--------|
| | |
| V_{CC} supply voltage -0.5 +4.6 | S V |
| I_{IK} input clamping current $V_I < 0 \text{ V}$ -50 - | mA |
| V _I input voltage 11 -0.5 +4.6 | 6 V |
| I_{OK} output clamping current $V_O < 0 \text{ V}$ -50 - | mA |
| V _O output voltage Active mode and Power-down mode [1] -0.5 +4.6 | 6 V |
| I_{O} output current $V_{O} = 0 \text{ V to } V_{CC}$ - ± 20 | mA |
| I _{CC} supply current - 50 | mA |
| I _{GND} ground current -50 - | mA |
| T _{stg} storage temperature –65 +15 | 0 °C |
| P_{tot} total power dissipation $T_{amb} = -40 ^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$ [2] - 250 | mW |

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 7. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------|---------------------|--|-----|----------|------|
| V_{CC} | supply voltage | | 2.3 | 3.6 | V |
| V _I | input voltage | | 0 | 3.6 | V |
| Vo | output voltage | Active mode | 0 | V_{CC} | V |
| | | Power-down mode; V _{CC} = 0 V | 0 | 3.6 | V |
| T_{amb} | ambient temperature | | -40 | +125 | °C |

^[2] For SC-88 package: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|--|--------------|-----|------|------|
| T _{amb} = 2 | 25 °C | | | | | |
| V_{T+} | positive-going threshold | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.60 | - | 1.10 | V |
| | voltage | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 0.75 | - | 1.16 | V |
| V_{T-} | negative-going threshold | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.35 | - | 0.60 | V |
| | voltage | V _{CC} = 3.0 V to 3.6 V | 0.50 | - | 0.85 | V |
| V _H | hysteresis voltage | $(V_H = V_{T+} - V_{T-})$ | | | | |
| | | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.23 | - | 0.60 | V |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 0.25 | - | 0.56 | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_{O} = -20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | $V_{CC}-0.1$ | - | - | V |
| | | $I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 2.05 | - | - | V |
| | | $I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.9 | - | - | V |
| | | $I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.72 | - | - | V |
| | | $I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.6 | - | - | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_O = 20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | - | - | 0.10 | V |
| | | $I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.31 | V |
| | | $I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.44 | V |
| | | $I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.31 | V |
| | | $I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.44 | V |
| I _I | input leakage current | $V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V | - | - | ±0.1 | μΑ |
| I _{OFF} | power-off leakage current | V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V | - | - | ±0.1 | μΑ |
| ΔI_{OFF} | additional power-off leakage current | V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V | - | - | ±0.2 | μΑ |
| I _{CC} | supply current | $V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | - | - | 1.2 | μΑ |
| Cı | input capacitance | $V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_I = \text{GND or } V_{CC}$ | - | 8.0 | - | pF |
| Co | output capacitance | $V_O = GND$; $V_{CC} = 0 V$ | - | 1.7 | - | pF |
| T _{amb} = - | 40 °C to +85 °C | | | | | |
| V _{T+} | positive-going threshold | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.60 | - | 1.10 | V |
| | voltage | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 0.75 | - | 1.19 | V |
| V_{T-} | negative-going threshold | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.35 | - | 0.60 | V |
| v - | voltage | V _{CC} = 3.0 V to 3.6 V | 0.50 | - | 0.85 | V |
| V _H | hysteresis voltage | $(V_{H} = V_{T+} - V_{T-})$ | | | | |
| | | V _{CC} = 2.3 V to 2.7 V | 0.10 | - | 0.60 | V |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | | | | |

Low-power configurable gate with voltage-level translator

Table 8. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|---|------------------------|-----|--------------------|------------------|
| V _{OH} | HIGH-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_O = -20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | $V_{CC}-0.1$ | - | - | V |
| | | $I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.97 | - | - | V |
| | | $I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.85 | - | - | V |
| | | $I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.67 | - | - | V |
| | | $I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.55 | - | - | V |
| / _{OL} | LOW-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_O = 20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | - | - | 0.1 | V |
| | | $I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.33 | V |
| | | $I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.45 | V |
| | | $I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.33 | V |
| | | $I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.45 | V |
| I | input leakage current | $V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V | - | - | ±0.5 | μΑ |
| OFF | power-off leakage current | V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V | - | - | ±0.5 | μΑ |
| ∆l _{OFF} | additional power-off leakage current | V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V | - | - | ±0.5 | μΑ |
| CC | supply current | V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 2.3 V to 3.6 V | - | - | 1.5 | μΑ |
| Δl _{CC} | additional supply current | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V; } I_{O} = 0 \text{ A}$ | [1] - | - | 4 | μΑ |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } I_{O} = 0 \text{ A}$ | [2] _ | - | 12 | μΑ |
| T _{amb} = - | 40 °C to +125 °C | | | | | |
| V _{T+} | positive-going threshold | V _{CC} = 2.3 V to 2.7 V | 0.60 | - | 1.10 | V |
| | voltage | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 0.75 | - | 1.19 | V |
| V_{T-} | negative-going threshold | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.33 | - | 0.64 | V |
| | voltage | V _{CC} = 3.0 V to 3.6 V | 0.46 | - | 0.85 | V |
| √ _H | hysteresis voltage | $(V_H = V_{T+} - V_{T-})$ | | | | |
| | | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | 0.10 | - | 0.60 | V |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 0.15 | - | 0.56 | V |
| √он | HIGH-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_{O} = -20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | V _{CC} - 0.11 | - | - | V |
| | | $I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.77 | - | - | V |
| | | $I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.67 | - | - | V |
| | | $I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.40 | - | - | V |
| | | $I_{O} = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$ | 2.30 | - | - | V |
| √ _{OL} | LOW-level output voltage | $V_I = V_{T+}$ or V_{T-} | | | | |
| | | $I_O = 20 \mu A$; $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$ | - | - | 0.11 | V |
| | | $I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.36 | V |
| | | $I_{\rm O} = 3.1 \text{ mA; } V_{\rm CC} = 2.3 \text{ V}$ | - | - | 0.50 | V |
| | | $I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.36 | V |
| | | $I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.50 | V |
| I | input leakage current | $V_1 = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$ | - | - | ±0.75 | μΑ |
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| | ata sheet | Rev. 2 — 18 October 2010 | | | 2 3 20.0.7 | 7 of 2 |

Low-power configurable gate with voltage-level translator

 Table 8.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|---|---|--------------|-----|-------|------|
| I _{OFF} | power-off leakage current | V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V | - | - | ±0.75 | μΑ |
| ΔI_{OFF} | additional power-off leakage current | V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V | - | - | ±0.75 | μА |
| I _{CC} | supply current | V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 2.3 V to 3.6 V | - | - | 3.5 | μА |
| ΔI_{CC} | additional supply current | V_{CC} = 2.3 V to 2.7 V; I_O = 0 A | <u>[1]</u> - | - | 7 | μΑ |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}; I_{O} = 0 \text{ A}$ | [2] _ | - | 22 | μΑ |

^[1] One input at 0.3 V or 1.1 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

| Symbol | Parameter | Conditions | | 25 °C | | | –40 °C to +125 °C | | | Unit |
|-----------------|------------------------------------|-----------------------------|-----|-------|--------|-----|-------------------|----------------|-----------------|------|
| | | | | Min | Typ[1] | Max | Min | Max (85 °C) | Max (125 °C) | |
| $V_{CC} = 2.3$ | 3 V to 2.7 V; V _I = 1.6 | 65 V to 1.95 V | | | | | | | | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | [2] | | | | | | | |
| | | $C_L = 5 pF$ | | 2.2 | 3.5 | 5.5 | 0.5 | 6.8 | 7.5 | ns |
| | | $C_L = 10 pF$ | | 2.6 | 4.1 | 6.3 | 1.0 | 7.9 | 8.7 | ns |
| | | $C_L = 15 pF$ | | 2.9 | 4.6 | 6.9 | 1.0 | 8.7 | 9.6 | ns |
| | | $C_L = 30 pF$ | | 3.7 | 5.8 | 8.4 | 1.5 | 10.8 | 11.9 | ns |
| $V_{CC} = 2.$ | 3 V to 2.7 V; V _I = 2.3 | 3 V to 2.7 V | | | | | | | | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | [2] | | | | | | | |
| | | $C_L = 5 pF$ | | 1.8 | 3.4 | 5.5 | 0.5 | 6.0 | 6.6 | ns |
| | | $C_L = 10 pF$ | | 2.2 | 4.0 | 6.2 | 1.0 | 7.1 | 7.9 | ns |
| | | $C_L = 15 pF$ | | 2.5 | 4.4 | 6.8 | 1.0 | 7.9 | 8.7 | ns |
| | | $C_L = 30 pF$ | | 3.2 | 5.6 | 8.3 | 1.5 | 10.0 | 11.0 | ns |
| $V_{CC} = 2.$ | 3 V to 2.7 V; V _I = 3.0 |) V to 3.6 V | | | | | | | | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | [2] | | | | | | | |
| | | $C_L = 5 pF$ | | 1.4 | 3.1 | 5.0 | 0.5 | 5.5 | 6.1 | ns |
| | | $C_L = 10 pF$ | | 1.8 | 3.7 | 5.7 | 1.0 | 6.5 | 7.2 | ns |
| | | $C_L = 15 pF$ | | 2.2 | 4.2 | 6.3 | 1.0 | 7.4 | 8.2 | ns |
| | | $C_L = 30 pF$ | | 2.9 | 5.3 | 7.9 | 1.5 | 9.5 | 10.5 | ns |
| $V_{CC} = 3.$ | 0 V to 3.6 V; V _I = 1.6 | 65 V to 1.95 V | | | | | | | | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | [2] | | | | | | | |
| | | $C_L = 5 pF$ | | 2.1 | 2.9 | 3.9 | 0.5 | 8.0 | 8.8 | ns |
| | | C _L = 10 pF | | 2.5 | 3.4 | 4.6 | 1.0 | 8.5 | 9.4 | ns |
| | | C _L = 15 pF | | 2.9 | 3.9 | 5.2 | 1.0 | 9.1 | 10.1 | ns |
| | | $C_L = 30 \text{ pF}$ | | 3.6 | 5.0 | 6.7 | 1.5 | 9.8 | 10.8 | ns |

^[2] One input at 0.45 V or 1.2 V, other input at V_{CC} or GND.

Low-power configurable gate with voltage-level translator

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

| Symbol | Parameter | Conditions | | 25 °C | | | −40 °C to +125 °C | | |
|----------------------|------------------------------------|--|-----------|--------|-----|-----|-------------------|-----------------|----|
| | | | Min | Typ[1] | Max | Min | Max (85 °C) | Max (125 °C) | |
| $V_{CC} = 3$. | 0 V to 3.6 V; V _I = 2.3 | 3 V to 2.7 V | ' | ' | | 1 | | 1 | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | <u>?]</u> | | | | | | |
| | | C _L = 5 pF | 1.7 | 2.8 | 4.2 | 0.5 | 5.3 | 5.9 | ns |
| | | C _L = 10 pF | 2.1 | 3.4 | 5.0 | 1.0 | 6.1 | 6.8 | ns |
| | | C _L = 15 pF | 2.4 | 3.8 | 5.6 | 1.0 | 6.8 | 7.5 | ns |
| | | $C_L = 30 \text{ pF}$ | 3.2 | 5.0 | 7.1 | 1.5 | 8.5 | 9.4 | ns |
| $V_{CC} = 3$. | 0 V to 3.6 V; V _I = 3.0 |) V to 3.6 V | | | | | | | |
| t _{pd} | propagation delay | A, B, C to Y; see Figure 12 | <u>?]</u> | | | | | | |
| | | C _L = 5 pF | 1.4 | 2.7 | 4.2 | 0.5 | 4.7 | 5.2 | ns |
| | | C _L = 10 pF | 1.8 | 3.3 | 5.0 | 1.0 | 5.7 | 6.3 | ns |
| | | C _L = 15 pF | 2.1 | 3.8 | 5.6 | 1.0 | 6.2 | 6.9 | ns |
| | | C _L = 30 pF | 2.9 | 4.9 | 7.1 | 1.5 | 7.8 | 8.6 | ns |
| T _{amb} = 2 | 5 °C | | | | | | | | |
| C_{PD} | power dissipation | $f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ | <u>B]</u> | | | | | | |
| | capacitance | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | - | 3.6 | - | - | - | - | pF |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | - | 4.3 | - | - | - | - | pF |

^[1] All typical values are measured at nominal V_{CC}.

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

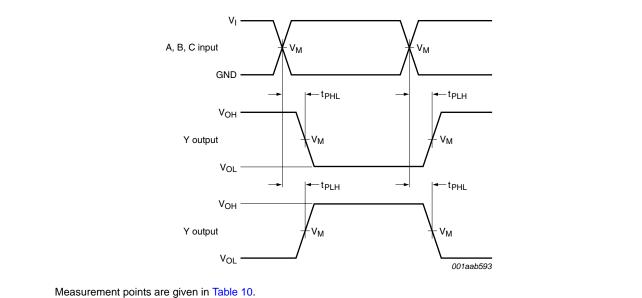
^[2] t_{pd} is the same as t_{PLH} and t_{PHL}

^[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

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12. Waveforms



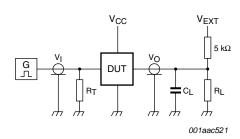
 V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 12. Input A, B and C to output Y propagation delay times.

Table 10. Measurement points

| Supply voltage | Output | Input | | |
|-----------------|--------------------|-------------------|-----------------|-------------|
| V _{CC} | V _M | V _M | V _I | $t_r = t_f$ |
| 2.3 V to 3.6 V | 0.5V _{CC} | 0.5V _I | 1.65 V to 3.6 V | ≤ 3.0 ns |

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Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 13. Test circuit for measuring switching times

Table 11. Test data

| Supply voltage | Load | | V _{EXT} | | |
|-----------------|------------------------------|------------------------------|-------------------------------------|-------------------------------------|-------------------------------------|
| V _{CC} | C _L | R _L [1] | t _{PLH} , t _{PHL} | t _{PZH} , t _{PHZ} | t _{PZL} , t _{PLZ} |
| 2.3 V to 3.6 V | 5 pF, 10 pF, 15 pF and 30 pF | 5 k Ω or 1 M Ω | open | GND | $2\times V_{CC}$ |

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

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13. Package outline

Plastic surface-mounted package; 6 leads

SOT363

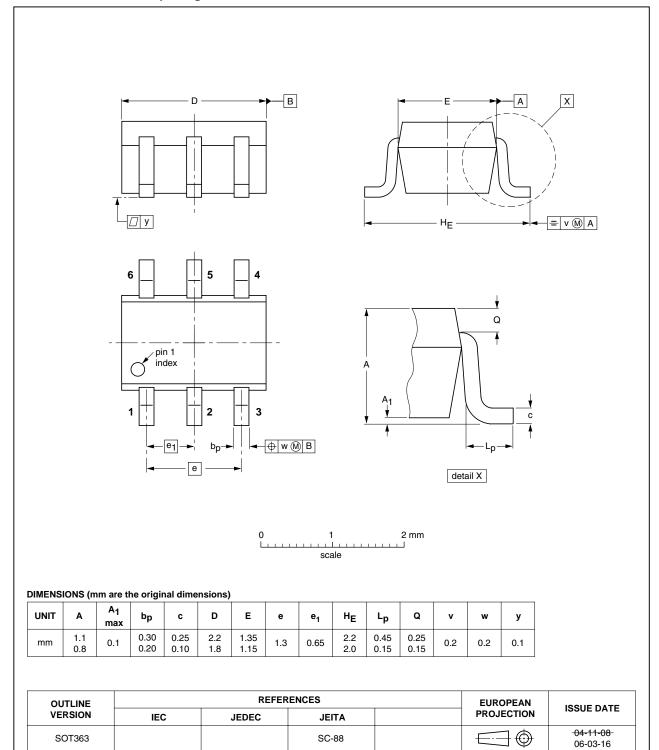


Fig 14. Package outline SOT363 (SC-88)

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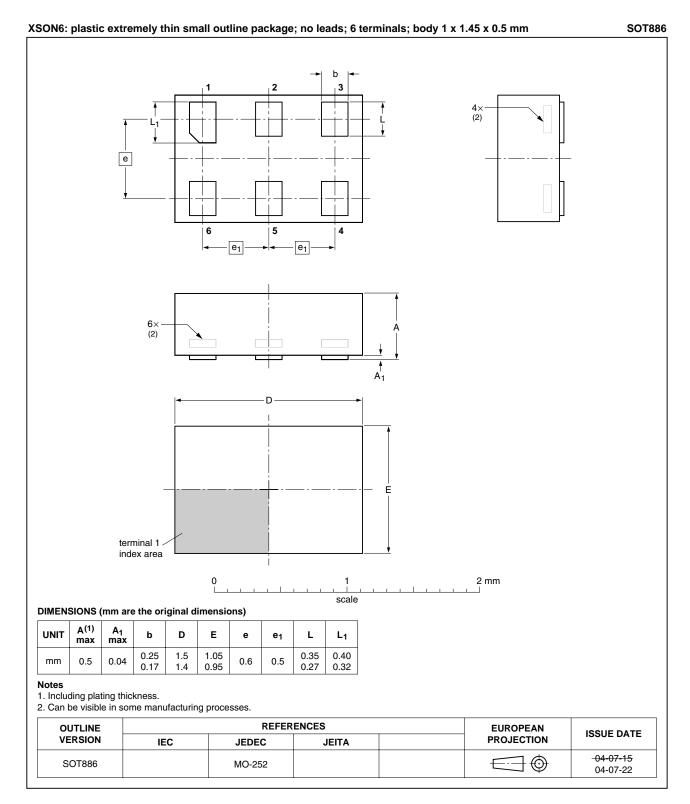


Fig 15. Package outline SOT886 (XSON6)

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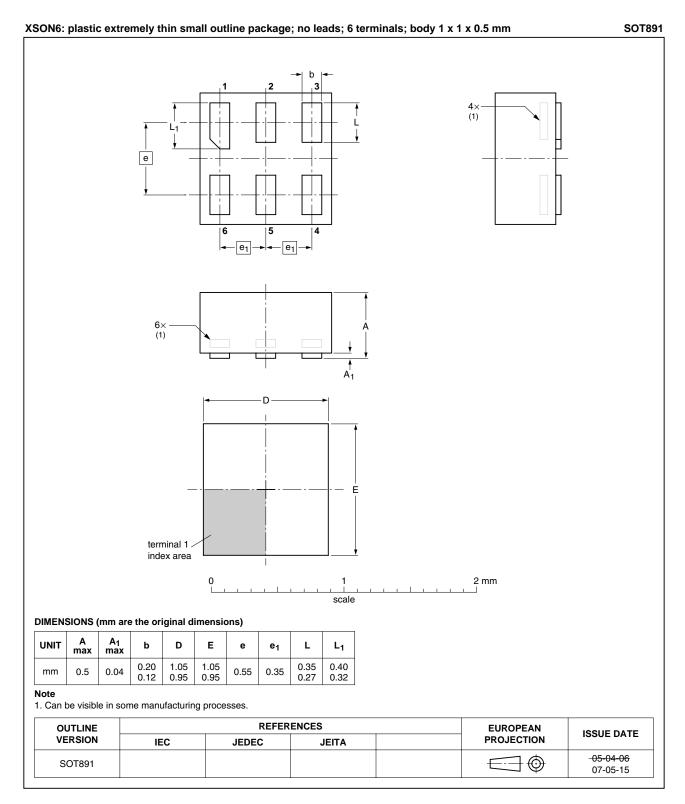


Fig 16. Package outline SOT891 (XSON6)

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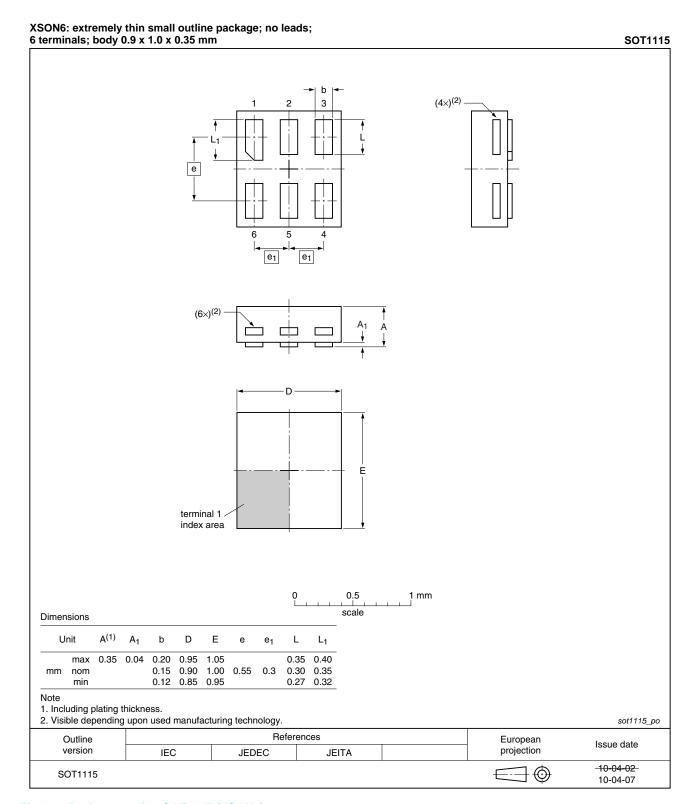


Fig 17. Package outline SOT1115 (XSON6)

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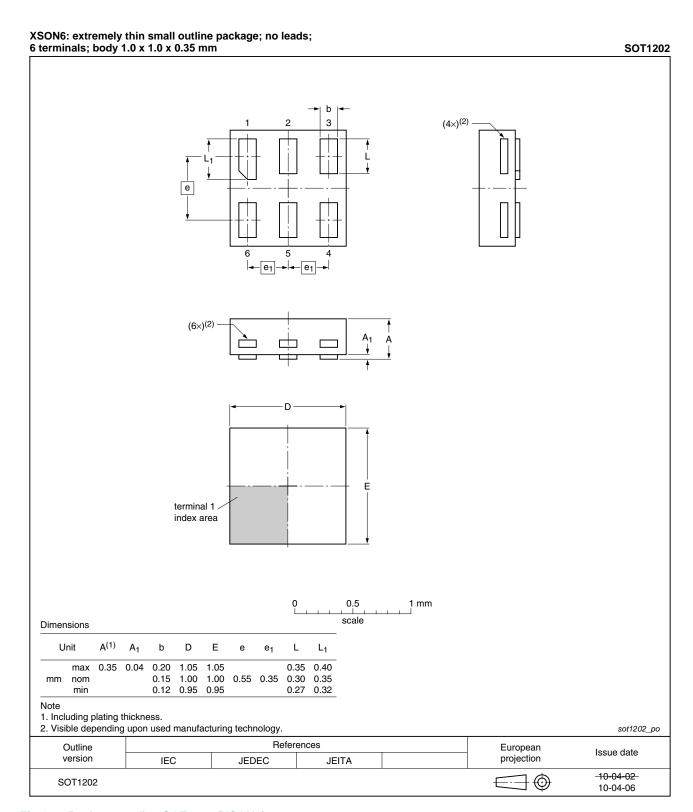


Fig 18. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 12. Abbreviations

| Acronym | Description |
|---------|---|
| CDM | Charged Device Model |
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |

15. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|--------------------|---------------|---------------|
| 74AUP1T97 v.2 | 20101018 | Product data sheet | - | 74AUP1T97 v.1 |
| Modifications: | Added type number 74AUP1T97GN (SOT1115/XSON6 package). Added type number 74AUP1T97GS (SOT1202/XSON6 package). | | | |
| 74AUP1T97 v.1 | 20071025 | Product data sheet | - | - |

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16. Legal information

16.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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